

THE SPECIFICATION OF AlGaAs IR LED CHIP “YL-C880nM-4mW”

1. DESCRIPTION

This is a AlGaAs infrared LED chip. It is N-side up. The peak wavelength is 880 nm (Typ.).

2. ELECTRO - OPTICAL CHARACTERISTICS (Ta=25 deg.C)

CONDITION	Symbol	Condition	MIN.	TYP.	MAX.	UNIT
Forward Voltage	V _f	IF=20mA		1.42		V
Reverse Voltage	V _r	IR=10uA	5			V
Radiated Power ¹⁾	P _o	IF=20mA	4.0			mW
Peak Wavelength	λ	IF=20mA	875	880	892	nm
Spectral Radiation Bandwidth		IF=20mA		55		nm
Rise Time	T _r	IF _p =100mA T _w =125ns,Duty=25%		20		ns
Fall Time	T _f	IF _p =100mA T _w =125ns,Duty=25%		20		ns
Peak Forward Voltage	V _{fm}	IF _p =200mA T _w =10us,Duty=10%		2.05		V

1) LED chip is mounted on TO-18 gold header without resin coated.

3. ABSOLUTE MAXIMUM RATINGS

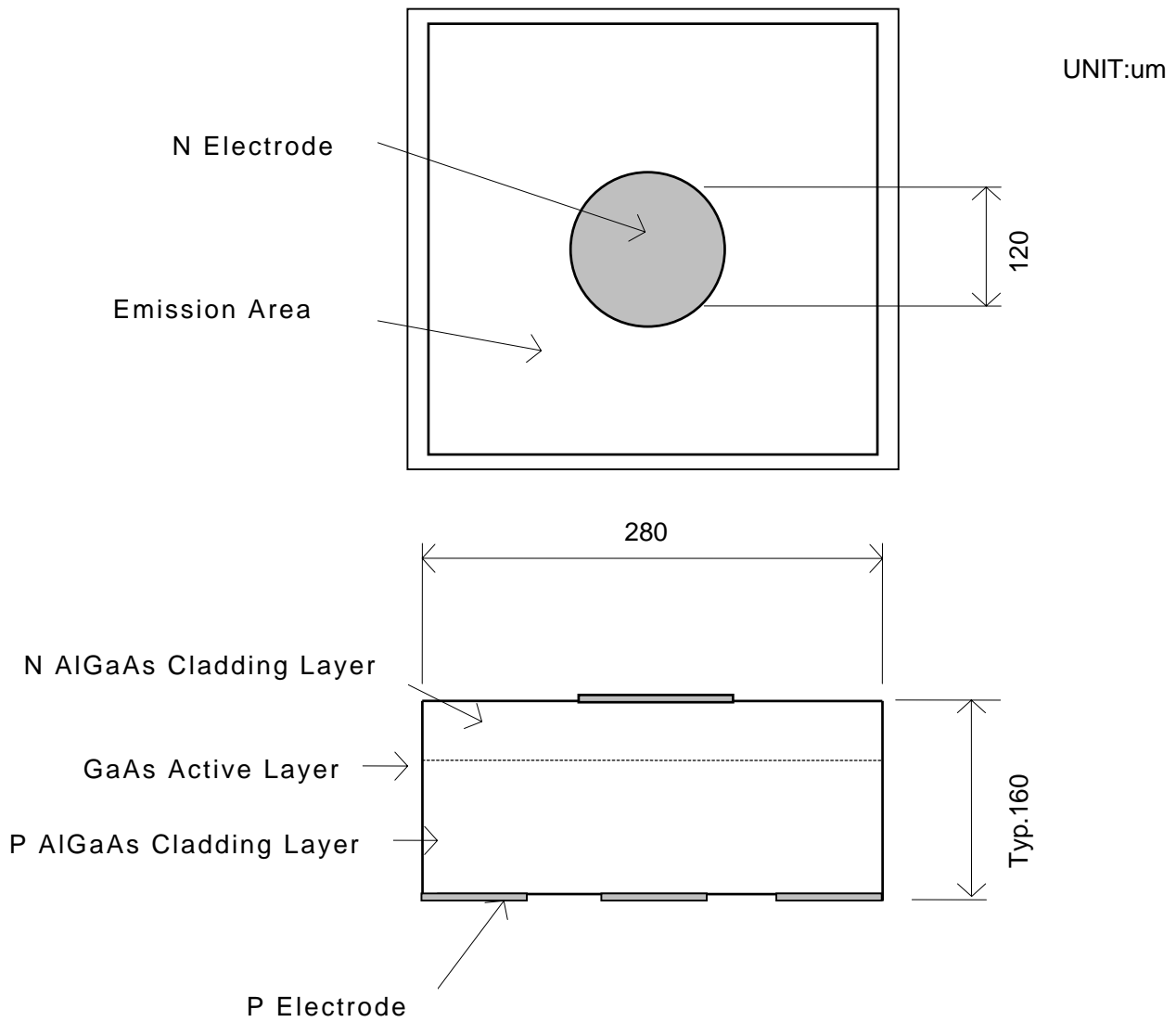
Continuous Maximum Forward Current : 80 mA(DC)
 Reverse Voltage : 5 V(IR=10uA)
 Storage Temperature
 while on mylar membrane : 0 to 40 deg. C
 after removal from mylar membrane : -40 to 100 deg. C

4. PHYSICAL CHARACTERISTICS AND STRUCTURE

1) Material : AlGaAs
 2) Structure : Double Hetero Structure
 3) Junction Size : 0.280mmX0.280mm
 4) Thickness : 0.160mm
 5) Bond Pad Size : 0.120mm diameter
 6) Anode Metallization : Gold Alloy
 7) Cathode Metallization: Gold Alloy

Physical Dimensions

Model YL-C880nM-4mW



Remark: This specification is for reference purpose only, and subject to change without prior notice.
Approved specification shall be obtained for the regular purchase.